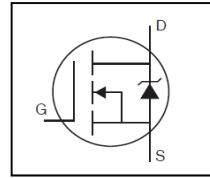


- Logic –Level Gate Drive
- Advanced Process Technology
- Isolated Package
- High Voltage Isolation = 2.5KVRMS ⑤
- Sink to Lead Creepage Dist. = 4.8mm
- Fully Avalanche Rated
- Lead-Free

HEXFET® Power MOSFET



V_{DSS}	55V
$R_{DS(on)}$	0.035Ω
I_D	22A



G	D	S
Gate	Drain	Source

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-220 Full Pak eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heat sink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The Fullpak is mounted to a heat sink using a single clip or by a single screw fixing.

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRLIZ34NPbF	TO-220 Full-Pak	Tube	50	IRLIZ34NPbF

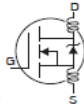
Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	22	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	15	
I_{DM}	Pulsed Drain Current ①⑥	110	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	37	W
	Linear Derating Factor	0.24	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②⑥	110	mJ
I_{AR}	Avalanche Current ①⑥	16	A
E_{AR}	Repetitive Avalanche Energy ①⑥	3.7	mJ
dv/dt	Peak Diode Recovery dv/dt③⑥	5.0	V/ns
T_J	Operating Junction and Storage Temperature Range	-55 to + 175	°C
T_{STG}			
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf·in (1.1N·m)	

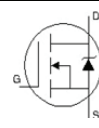
Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	4.1	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	65	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

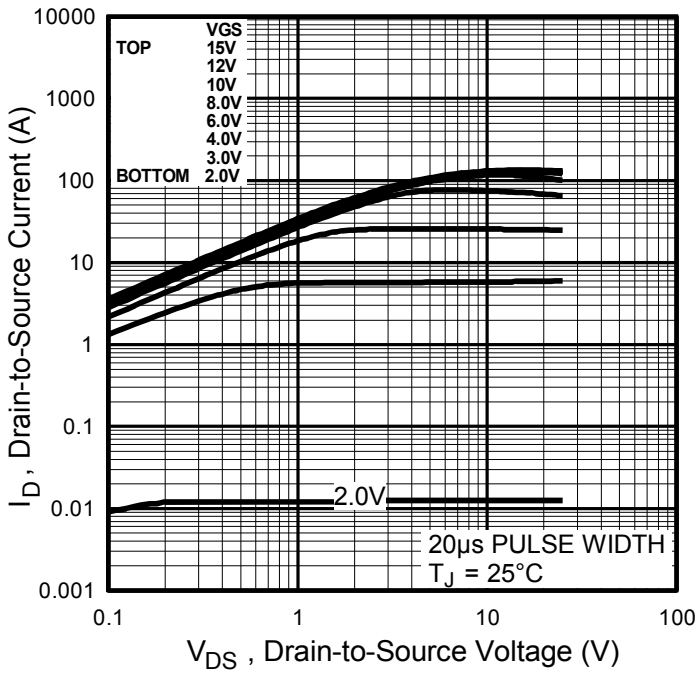
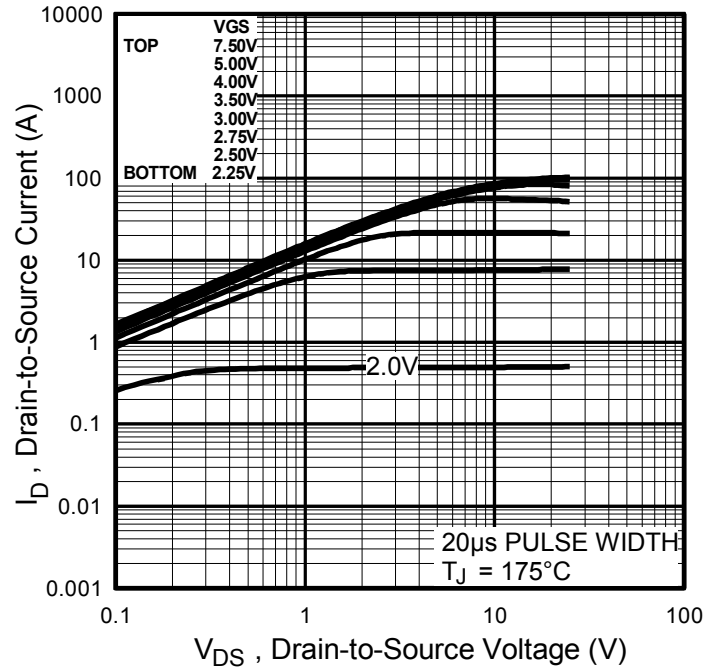
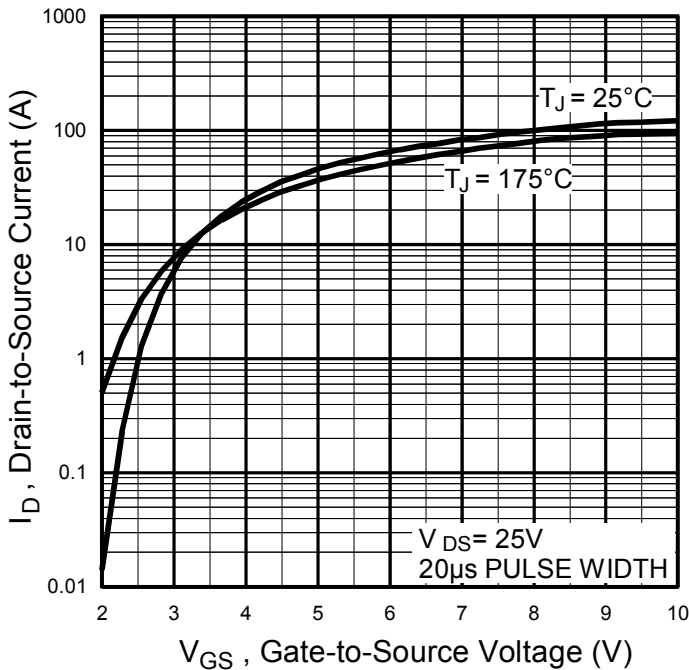
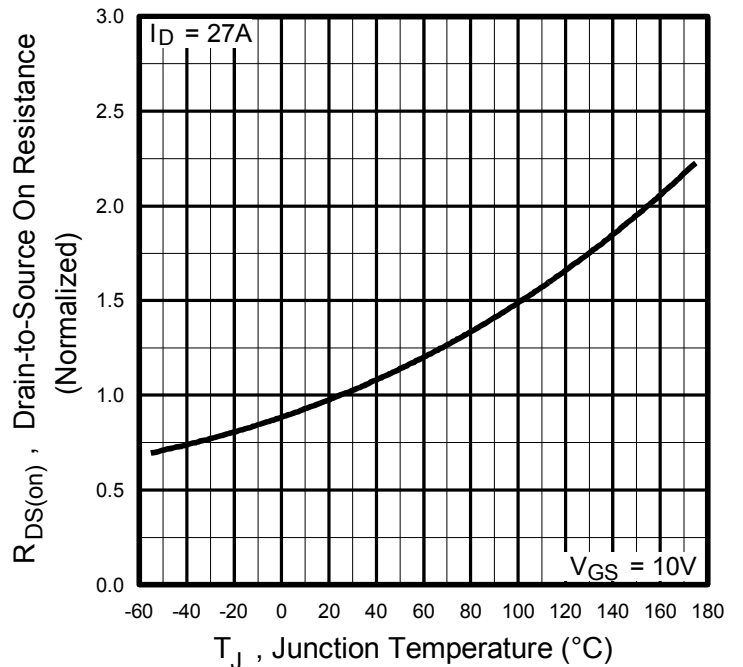
	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.065	—	V/°C	Reference to 25°C, I _D = 1mA ⑥
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.035	Ω	V _{GS} = 10V, I _D = 12A
		—	—	0.046		V _{GS} = 5.0V, I _D = 12A
		—	—	0.060		V _{GS} = 4.0V, I _D = 10A
V _{GS(th)}	Gate Threshold Voltage	1.0	—	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Trans conductance	11	—	—	S	V _{DS} = 25V, I _D = 16A⑥
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 55V, V _{GS} = 0V
		—	—	250		V _{DS} = 44V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -16V
Q _g	Total Gate Charge	—	—	25	nC	I _D = 16A
Q _{gs}	Gate-to-Source Charge	—	—	5.2		V _{DS} = 44V
Q _{gd}	Gate-to-Drain Charge	—	—	14		V _{GS} = 5.0V, See Fig. 6 and 13④⑥
t _{d(on)}	Turn-On Delay Time	—	8.9	—	ns	V _{DD} = 28V
t _r	Rise Time	—	100	—		I _D = 16A
t _{d(off)}	Turn-Off Delay Time	—	29	—		R _G = 6.5Ω, V _{GS} = 5.0V
t _f	Fall Time	—	21	—		R _D = 1.8Ω, See Fig. 10④⑥
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	880	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	220	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	94	—		f = 1.0MHz, See Fig. 5⑥
C	Drain to Sink Capacitance	—	12	—		f = 1.0MHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	22	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①⑥	—	—	110		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 12A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	76	110	ns	T _J = 25°C, I _F = 16A
Q _{rr}	Reverse Recovery Charge	—	190	290	nC	di/dt = 100A/μs ④⑥

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② V_{DD} = 25V, Starting T_J = 25°C, L = 610μH, R_G = 25Ω, I_{AS} = 16A (See fig. 12)
- ③ I_{SD} ≤ 16A, di/dt ≤ 270A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ t = 60s, f = 60Hz
- ⑥ Uses IRLZ34N data and test conditions.


Fig. 1 Typical Output Characteristics

Fig. 2 Typical Output Characteristics

Fig. 3 Typical Transfer Characteristics

Fig. 4 Normalized On-Resistance vs. Temperature

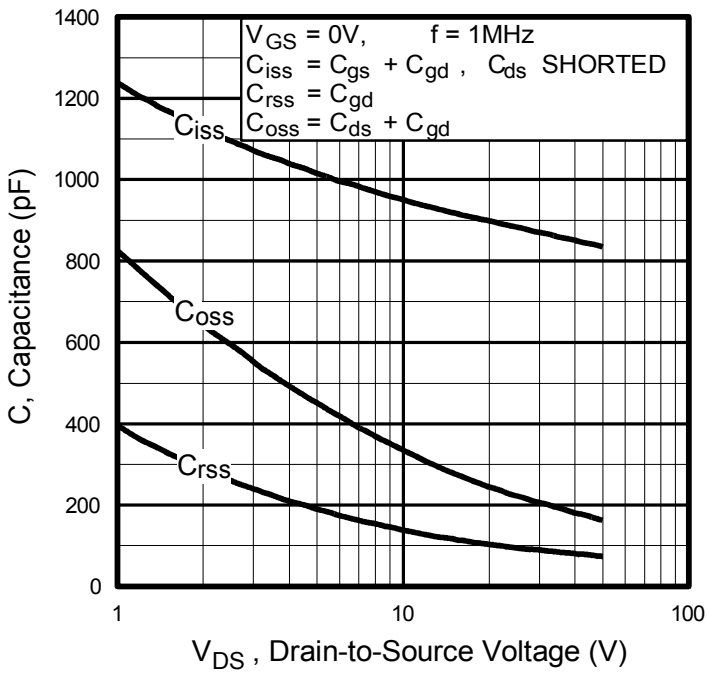


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

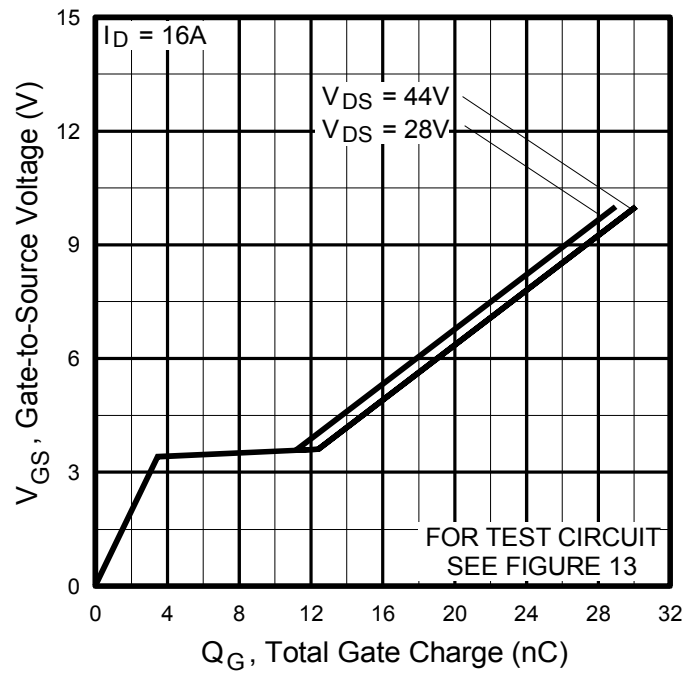


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

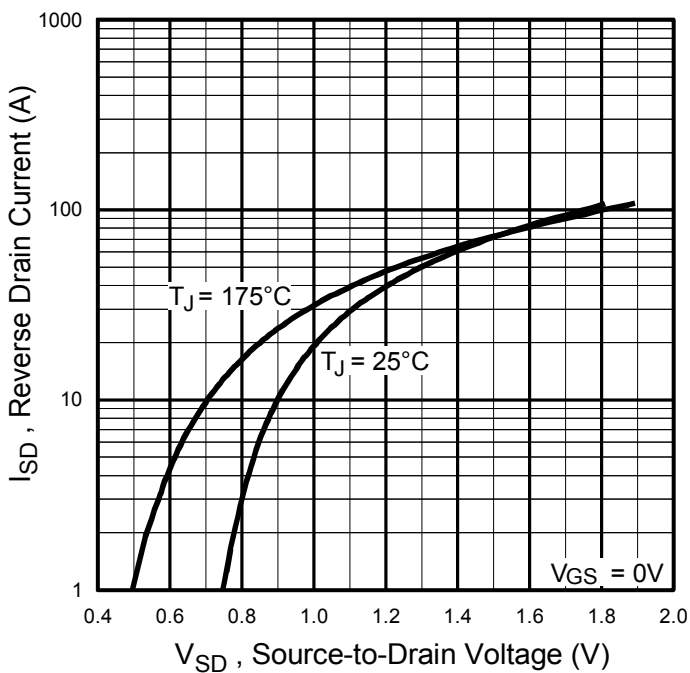


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

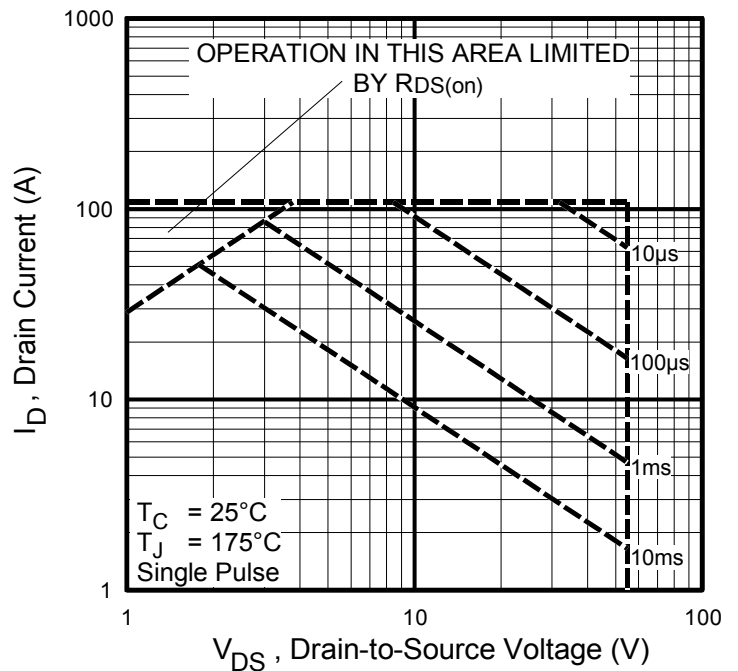


Fig 8. Maximum Safe Operating Area

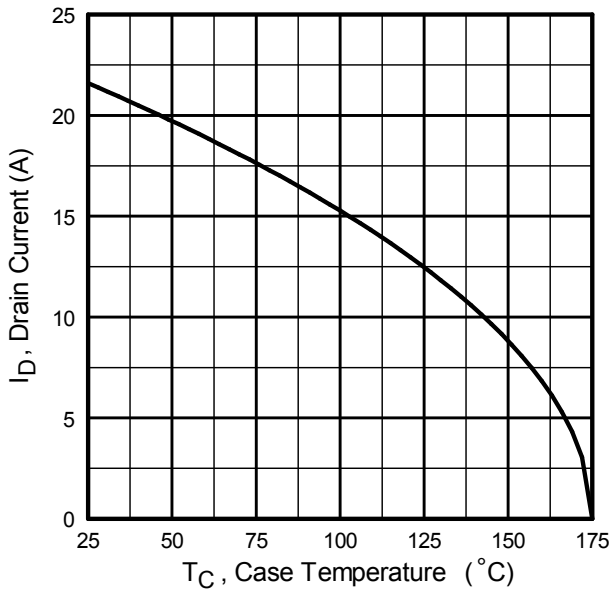
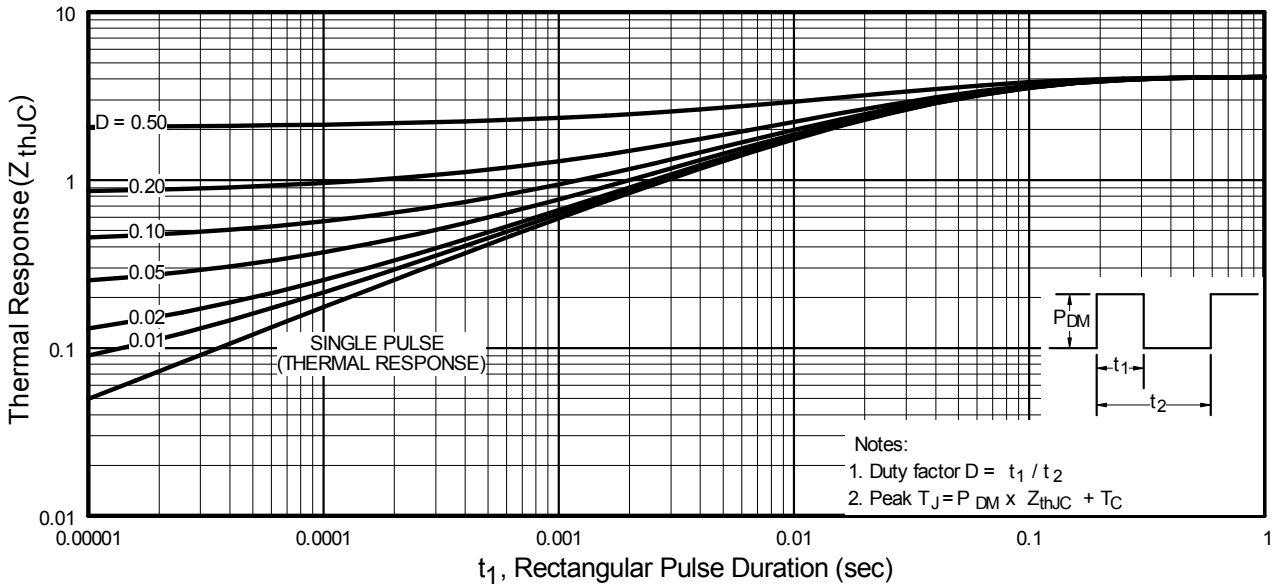

Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10a. Switching Time Test Circuit

Fig 10b. Switching Time Waveforms

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

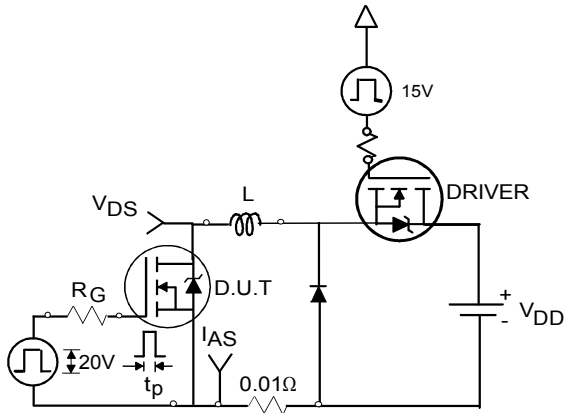
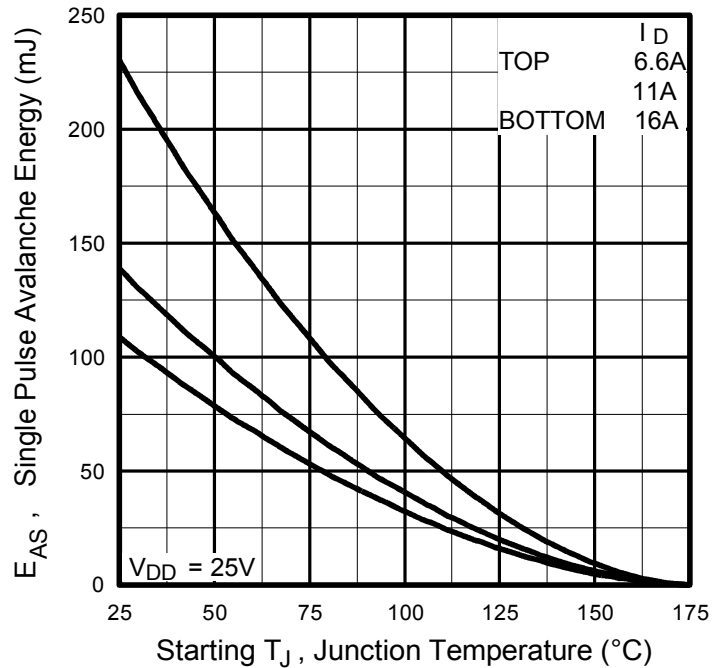
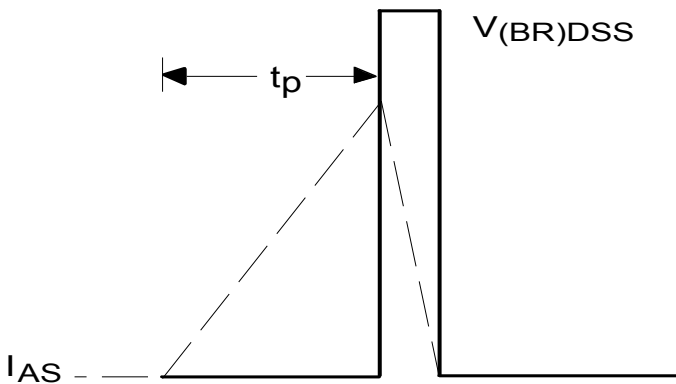
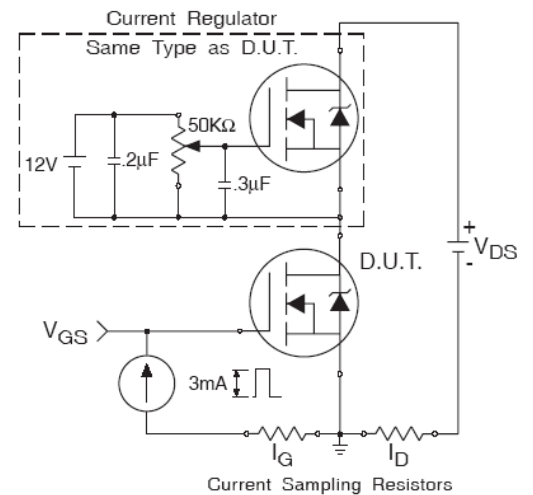

Fig 12a. Unclamped Inductive Test Circuit

Fig 12c. Maximum Avalanche Energy vs. Drain Current

Fig 12b. Unclamped Inductive Waveforms

Fig 13a. Gate Charge Waveform

Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

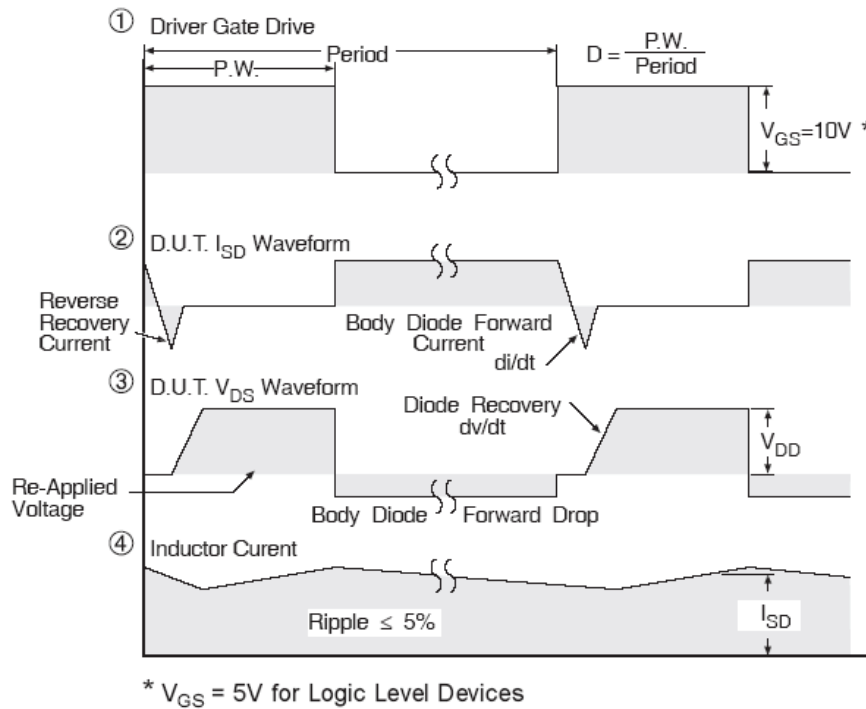
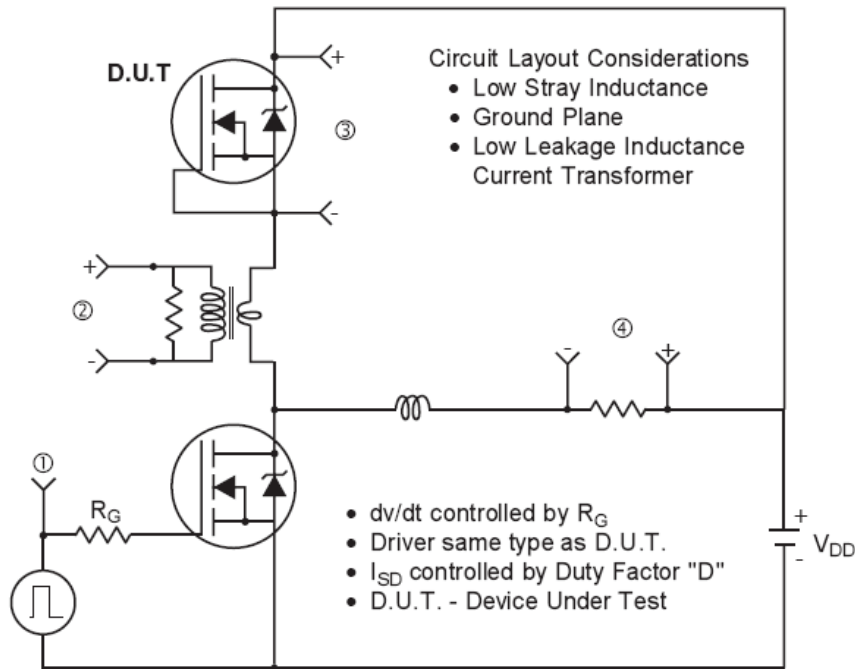
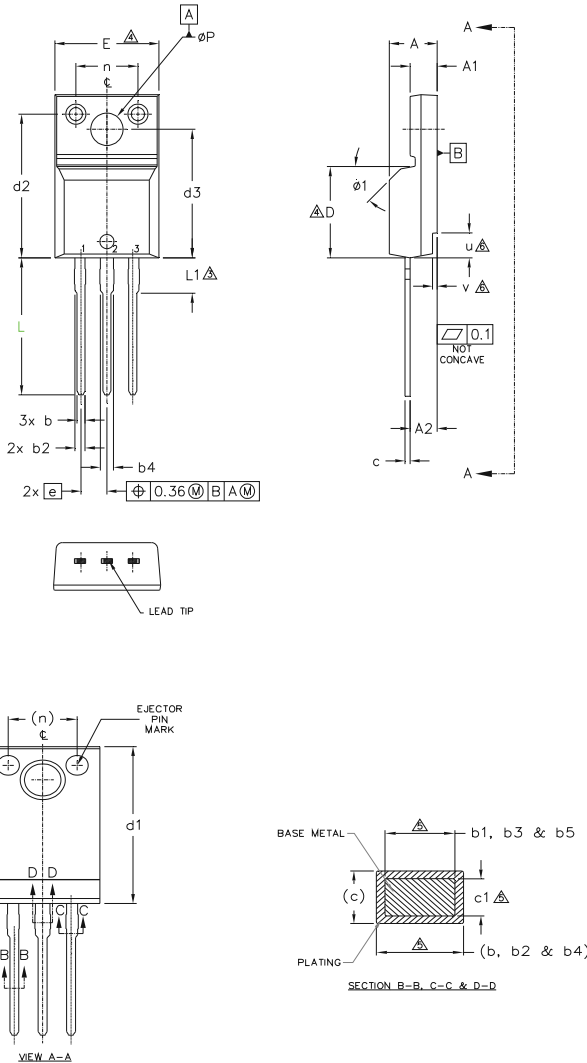


Fig 14. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

TO-220 Full-Pak Package Outline (Dimensions are shown in millimeters (inches))

NOTES:

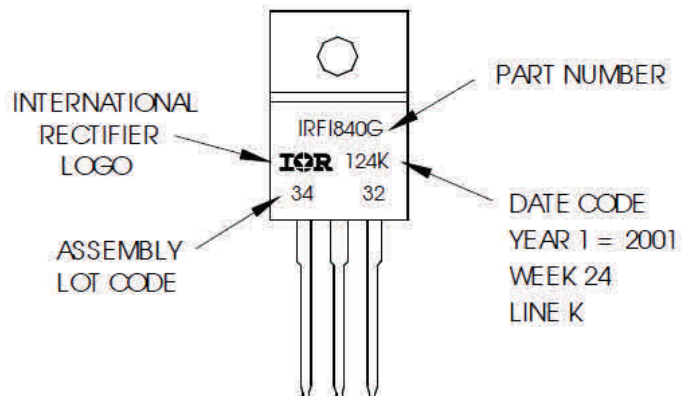
- 1.0 DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.
- 5.0 DIMENSION b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.
- 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
- 7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.57	4.83	.180	.190	LEAD ASSIGNMENTS <u>HEXFET</u> 1.- GATE 2.- DRAIN 3.- SOURCE
A1	2.57	2.82	.101	.111	
A2	2.51	2.92	.099	.115	
b	0.61	0.94	.024	.037	
b1	0.61	0.89	.024	.035	
b2	0.76	1.27	.030	.050	
b3	0.76	1.22	.030	.048	
b4	1.02	1.52	.040	.060	
b5	1.02	1.47	.040	.058	
c	0.33	0.63	.013	.025	
c1	0.33	0.58	.013	.023	5
D	8.66	9.80	.341	.386	4
d1	15.80	16.13	.622	.635	IGBTs, CoPACK 1.- GATE 2.- COLLECTOR 3.- EMITTER
d2	13.97	14.22	.550	.560	
d3	12.29	12.93	.484	.509	
E	9.63	10.74	.379	.423	4
e	2.54 BSC		.100 BSC		3
L	13.21	13.72	.520	.540	
L1	3.10	3.68	.122	.145	6
n	6.05	6.60	.238	.260	
øP	3.05	3.45	.120	.136	6
u	2.39	2.49	.094	.098	
v	0.41	0.51	.016	.020	6
ø1	-	45°	-	45°	

TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G
WITH ASSEMBLY
LOT CODE 3432
ASSEMBLED ON WW 24, 2001
IN THE ASSEMBLY LINE "K"

Note: "P" in assembly line position
indicates "Lead-Free"



TO-220AB Full-Pak packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to website at <http://www.irf.com/package/>

Qualification Information

Qualification Level	Industrial (per JEDEC JESD47F) †	
Moisture Sensitivity Level	TO-220 Full-Pak	N/A
RoHS Compliant	Yes	

† Applicable version of JEDEC standard at the time of product release.

Revision History

Date	Comments
04/27/2017	<ul style="list-style-type: none"> Changed datasheet with Infineon logo - all pages. Corrected Package Outline on page 8. Added disclaimer on last page.

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Edition 2016-04-19

Published by

Infineon Technologies AG

81726 Munich, Germany

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